

Electronic Devices

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Contents

Chapter 1 Basics of Semiconductor

1.1	Introduction	1.1
1.2	Atomic Bond	1.2
1.3	Types of Material	1.3
1.4	Semiconductor Doping	1.4
1.4.1	Trivalent doping	1.5
1.4.2	Pentavalent doping	1.6
1.5	Majority Carrier Current Analysis	1.6
1.5.1	Drift current	1.6
1.5.2	Diffusion current	1.7
1.5.3	Total current density in a semiconductor	1.8
	Review Questions	1.9

Chapter 2 Semiconductor Diode

2.1 - 2.36

2.1	Junction Formation in Unbiased PN-Junction	2.1
2.1.1	n-type semiconductor	2.6
2.1.2	Effect of doping on depletion region	2.10
2.2	Diode Current Equation	2.11
2.3	Capacitance in PN-Junction	2.14
2.3.1	Depletion capacitance, C_T	2.14
2.3.2	Diffusion capacitance, C_D	2.17
2.4	Semiconductor Diode	2.19
2.4.1	Energy band analysis of pn -junction diode	2.19
2.5	Unbiased Diode	2.22
2.6	Biased Diode	2.22
2.6.1	Forward biased diode	2.22
2.6.2	Reverse biased diode	2.23
2.7	Diode Breakdown	2.23
2.7.1	Zener breakdown	2.24
2.7.2	Avalanche multiplication	2.24

2.7.3	Temperature effect on breakdown voltage	2.24
2.8	Diode Characteristics	2.25
2.9	Diode Resistance	2.26
2.10	Diode Rating	2.28
2.10.1	Peak inverse voltage	2.28
2.10.2	Maximum forward current	2.28
2.11	Diode Modelling	2.30
2.11.1	Switching characteristics of diode	2.31
	<i>Review Questions</i>	2.34

Chapter 3 Bipolar Junction Transistor

3.1 - 3.67

3.1	Introduction	3.1
3.1.1	Transistor terminals	3.1
3.2	Types of Transistor	3.2
3.2.1	n-p-n Transistor	3.2
3.2.2	p-n-p Transistor	3.3
3.2.3	Comparison of n-p-n and p-n-p transistor	3.3
3.3	Unbiased n-p-n Transistor	3.4
3.4	Biased n-p-n Transistor	3.5
3.4.1	Transistor in active region	3.6
3.4.2	Why named transistor	3.7
3.4.3	Transistor currents	3.7
3.4.4	Transistor under saturation region	3.9
3.4.5	Transistor in cut-off region	3.11
3.4.6	Base-width modulation	3.11
3.5	Transistor Configuration	3.12
3.5.1	Common-base configuration	3.13
3.5.2	Common-emitter configuration	3.15
3.5.3	Common-collector configuration	3.18
3.6	Transistor as a Switch	3.20
3.6.1	BJT at cut-off region	3.20
3.6.2	BJT at saturation region	3.21
3.6.3	Factors that contributes for delay time	3.23
3.6.4	Reason for storage time	3.23

3.7	Breakdown Characteristic of BJT	3.23
3.7.1	Avalanche breakdown	3.23
3.7.2	Reach-through	3.24
3.8	Ebers-Moll BJT Model	3.24
3.9	The Hybrid Parameter Model	3.27
3.10	h-Parameter model of BJT	3.28
3.10.1	h-parameter model of BJT for CB configuration	3.28
3.10.2	h-parameter model of BJT for CE configuration	3.29
3.10.3	h-parameter model of BJT for CC configuration	3.30
3.11	Amplifier Parameters using h-parameter Model	3.31
3.11.1	Current gain, \mathbf{A}_I	3.31
3.11.2	Input impedance, \mathbf{Z}_i	3.32
3.11.3	Voltage gain, \mathbf{A}_V	3.32
3.11.4	Voltage gain with source resistance, \mathbf{A}_{VS}	3.33
3.11.5	Current gain with source resistance, \mathbf{A}_{IS}	3.34
3.11.6	Output admittance \mathbf{Y}_0	3.35
3.12	Amplifier Parameters using Simplified h-parameter Model	3.36
3.12.1	Current gain, \mathbf{A}_I	3.36
3.12.2	Input impedance, \mathbf{Z}_i	3.37
3.12.3	Voltage gain, \mathbf{A}_V	3.37
3.12.4	Voltage gain with source resistance, \mathbf{A}_{VS}	3.37
3.12.5	Current gain with source resistance, \mathbf{A}_{IS}	3.37
3.13	h-parameter model Analysis of Common-Emitter Amplifier	3.37
3.13.1	Fixed bias circuit	3.38
3.13.2	Voltage-divider bias with bypass capacitor \mathbf{C}_E	3.41
3.13.3	Self bias or emitter-bias circuit without bypass capacitor .	3.44
3.14	h-parameter Model Analysis of Common Collector (Emitter-Follower) Configuration	3.48
3.14.1	Input impedance	3.49
3.14.2	Current gain	3.50
3.14.3	Output impedance	3.51
3.14.4	Voltage gain	3.53
3.15	h-parameter Model Analysis of Common Base Amplifier	3.54
3.15.1	Input impedance	3.54
3.15.2	Output impedance	3.55

3.15.3 Current gain	3.55
3.15.4 Voltage gain	3.55
3.16 Hybrid- π Model	3.56
3.17 Determination of hybrid- π parameters	3.57
3.17.1 Transconductance	3.57
3.17.2 Input conductance g_{be}	3.58
3.17.3 Feedback conductance g_{bc}	3.59
3.17.4 Base spreading resistance r_{bb}	3.59
3.17.5 Output conductance g_{ce}	3.60
3.18 Gummel Poon Model	3.60
3.18.1 Characteristic of Gummel-Poon model	3.64
3.19 Multi Emitter Transistor	3.65
<i>Review Questions</i>	3.66

Chapter 4 Field Effect Transistor 4.1 - 4.51

4.1 Introduction	4.1
4.1.1 Advantages of FET over BJT	4.2
4.1.2 Limitation of FET over BJT	4.2
4.2 Junction Field Effect Transistor	4.2
4.2.1 Characteristics of JFET	4.3
4.2.2 Mathematical analysis	4.6
4.3 Metal-Oxide Semiconductor Field Effect Transistor	4.10
4.3.1 Enhancement MOSFET	4.10
4.3.2 Characteristics of E-MOSFET	4.11
4.4 Depletion MOSFET	4.14
4.4.1 Characteristics of n-channel D-MOSFET	4.14
4.4.2 Comparison of p-MOS and n-MOS technology	4.17
4.4.3 Distinguish characteristics between E-MOSFET & D-MOSFET	4.17
4.4.4 VVR operations of FET	4.17
4.5 FET Modeling	4.18
4.6 Small Signal Model for FET	4.18
4.7 Small Signal Analysis of JFET in Common Source Configuration	4.19
4.7.1 Input impedance	4.20

4.7.2	Output impedance	4.20
4.7.3	Voltage gain	4.21
4.8	Self Bias Circuit with Bypass Capacitor C_s	4.21
4.8.1	Input impedance	4.22
4.8.2	Output impedance	4.23
4.8.3	Voltage gain	4.23
4.9	Self Bias Circuit of JFET without Bypass Capacitor	4.24
4.9.1	Input impedance	4.24
4.9.2	Output impedance	4.25
4.9.3	Voltage gain	4.27
4.10	Voltage-divider Bias of JFET	4.28
4.10.1	Input impedance	4.29
4.10.2	Output impedance	4.29
4.10.3	Voltage gain	4.30
4.11	Small Signal Model of Common Drain Configuration of JFET . .	4.30
4.11.1	Input impedance	4.31
4.11.2	Output impedance	4.32
4.11.3	Voltage gain	4.33
4.12	Small Signal Model of Common Gate Configuration of JFET . .	4.34
4.12.1	Input impedance	4.35
4.12.2	Output Impedance	4.36
4.12.3	Voltage gain	4.37
4.13	Depletion Type MOSFET	4.38
4.14	Small Signal Model of Enhancement Type MOSFET	4.38
4.15	Small Signal Analysis of Common Source Configuration of E-MOSFET with Voltage Feedback Bias	4.39
4.15.1	Input impedance	4.39
4.15.2	Output impedance	4.40
4.15.3	Voltage Gain	4.41
4.16	Common Source Configuration of E-MOSFET with Voltage Divider Bias	4.42
4.16.1	Input impedance	4.43
4.16.2	Output impedance	4.43
4.16.3	Voltage gain	4.43
4.17	FinFET	4.44

4.17.1 Construction	4.45
4.17.2 Fabrication of Silicon based FinFET	4.45
4.18 Dual Gate MOSFET	4.49
4.18.1 Construction	4.49
<i>Review Questions</i>	4.50
Chapter 5 Special Semiconductor Devices	5.1 - 5.19
5.1 Metal-Semiconductor Junction	5.1
5.2 Schottky Diode	5.1
5.3 MESFET	5.4
5.4 Tunnel Diode	5.7
5.5 Varactor Diode (VARICAP)	5.12
5.6 Uni-Junction Transistor	5.13
5.7 Zener Diodes	5.16
5.8 Avalanche Diodes	5.18
<i>Review Questions</i>	5.18
Chapter 6 Power Devices	6.1 - 6.18
6.1 Introduction	6.1
6.2 Silicon Controlled Rectifier	6.1
6.2.1 Two-transistor analogy of a SCR	6.2
6.2.2 Characteristics of a SCR	6.3
6.2.3 Applications	6.4
6.3 The TRIAC	6.4
6.4 The DIAC	6.6
6.4.1 Three-layer structure of DIAC	6.6
6.4.2 Five-layer structure of DIAC	6.7
6.5 Power BJT	6.8
6.6 Power MOSFET	6.11
6.7 VMOSFET	6.13
6.8 DMOS	6.15
<i>Review Questions</i>	6.17

Chapter 7 Photo Devices**7.1 - 7.43**

7.1	Introduction	7.1
7.2	Important Terms	7.1
7.2.1	Photoluminescence	7.1
7.2.2	Photoconductivity (Absorption)	7.2
7.2.3	Photoemissivity (Radiation)	7.2
7.2.4	Photovoltaic effect	7.2
7.3	Semiconductor Optoelectronic Devices	7.2
7.3.1	Homojunction and Heterojunction	7.4
7.3.2	Light Absorption and photo effect on frequency	7.5
7.4	Gallium Arsenide Devices	7.5
7.5	Light Dependent Resistor (LDR)	7.7
7.6	Photo Conducting Cell	7.7
7.7	Light Emitting Diode (LED)	7.11
7.8	LASER Diode	7.15
7.9	Liquid Crystal Display (LCD)	7.20
7.9.1	Dynamic scattering LCD (Transmittive mode)	7.21
7.9.2	Dynamic scattering LCD (Reflective mode)	7.22
7.9.3	Absorption mode LCD (Transmittive mode)	7.22
7.9.4	Absorption mode LCD (Reflective mode)	7.23
7.10	Photo Transistor	7.24
7.11	Opto-Isolator	7.26
7.12	Photovoltaic Cell (solar cell)	7.31
7.13	Charged Coupled Device	7.35
	<i>Review Questions</i>	7.41

Index**I.1 - I.2**